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Description

This invention relates to thin film transistors, thin film transistor arrays and to a method of preparing the same.

It has been known heretofore to utilize thin film transistors and particularly an array of thin film transistors to control and drive display panels such as, for example, liquid crystal displays, electroluminescent media and the like. Thin film transistors in this application offer an attractive substitute to the utilization of silicon technology because of the size limitation problems associated with that technology. A large number of thin film transistors can be prepared within any given area in a density satisfactory for pictorial presentation. Examples of thin film transistors and associated display panels are set forth in US—A—4,040,073 and 4,042,854.

Fabrication of thin film transistor arrays requires the generation of well-defined geometric patterns of metals, semiconductors and insulators. These are deposited in layers to form the transistor structures and circuit interconnections. Patterns can be generated by shadow masking or photolithographic methods. The first, a popular classic method, relies on a series of mechanical masks to define pattern geometries while shielding the remainder of the substrate from the deposition source. The photolithographic method is attractive for cost effective fabrication of large area circuits containing a high density of components.

It is known by those working in the field of thin film transistors that devices having more suitable characteristics are prepared when the interfaces between the various layers of the thin film transistors are prepared in a single vacuum pump-down. This is especially true of the layers which form the interface with the semiconductive layer of the thin film transistor. It is thought that the reason for this is that a freshly prepared clean surface, when forming the interface with the semiconductive layer, is desirable without being initially subjected to ambient conditions which may result in impurities or some form of degradation occurring to the surface structure. Thus, it is impossible to achieve a thin film transistor by the single pump-down technique where photolithographic techniques are employed in the fabrication of the layers next adjacent to the semiconductive layer. In the past, single pump-down techniques have been employed wherein a multiple number of shadow masks are employed within the vacuum system in order to deposit the proper shape of the different components of the thin film transistor during the single pump-down. This creates many problems because the multiple use of shadow masks has built-in limitations such as high initial capital expenditure, low ultimate panel size, and low resolution of the product, for example. Further, when one shadow mask is moved out of position between the substrate and the source of the material being deposited and a second moved in place, a registration problem employing very

close tolerances is present. When it is considered that in a thin film transistor array at least four thin film transistors are prepared per square mm (2,500 per square inch) of area, this registration problem is thereby greatly magnified.

It is therefore an object of this invention to provide a method of preparing thin film transistor arrays wherein the various layers are fabricated by a single pump-down technique without the use of multiple shadow mask steps.

US—A—4,040,073 shows a double gated thin film field effect transistor in which cadmium selenide is the semiconductor material. A thin layer of indium is provided on either side of the cadmium selenide conducting channel and after annealing enhances the transconductance of the device and reduces trapping of charge in the semiconductor. The source and drain contacts of the device are a combination of an indium layer and a copper layer which improve the performance of the device.

US—A—4,042,854 shows a large area integrated solid-state flat panel display in which thin film transistor addressing and drive circuitry is provided at each individual picture point with a display medium. The preferred display medium is an electroluminescent phosphor layer. An insulating layer of laminated photoresist is disposed over all electrical circuit elements except the electroluminescent drive electrodes.

US—A—4,086,127 discloses a method of fabricating apertured deposition masks with the masks being used in the fabrication of thin film deposited electronic components such as transistors. The masks comprise a core portion with a metal layer provided on a relief side of the core and a metal layer provided on the defining side of the core. The relief side metal layer and the core of the mask are further resist-delineated, selectively plated and etched differentially providing a mask preform in which the defining-side metal layer is left intact. A narrow width radiation beam is then directed upon closely-spaced portions of the defining side metal layer to cut selectively through the defining side metal layer providing the desired space apertures separated by a narrow bridge portion of the defining side metal layer.

US—A—3,669,661 discloses a process for producing a thin film transistor comprising, disposing a layer of a spacer material on one surface of a substrate, disposing a layer of a metal on said layer of spacer material, coating at least a portion of said metal layer with a layer of a photoresist material, exposing a pattern on said layer of photoresist material, developing said pattern on said layer of photoresist material, etching said pattern through to said one surface of the substrate, disposing said substrate in a vacuum chamber and sequentially vacuum depositing a plurality of materials through said etched pattern onto said surface of the substrate.

Accordingly, the invention contemplates a method of preparing an array of thin film transistors as claimed in the appended claims.

Thus, the invention contemplates depositing a semiconductive layer, discrete areas of an insulating material and a conducting layer over the insulating material and semiconductive layer in a single vacuum pump-down. This structure is then removed from vacuum and further processed in order to achieve a thin film transistor. Since only a single application of the insulating material is accomplished by deposition through a shadow mask, no registration problems are encountered. Further, the insulating material deposited through the shadow mask not only defines the conducting channel of the thin film transistor but protects the semiconductive material immediately adjacent thereto during the subsequent etching step of the subsequent photolithographic procedure.

Other objects and advantages of the present invention will become apparent from the following description with reference to the accompanying drawings, in which:

Fig. 1 is a cross-sectional view of a substrate being processed in accordance with a second embodiment of this invention;

Fig. 2 is a cross-sectional view of a substrate being processed in accordance with a second embodiment of this invention;

Fig. 3 is a cross-sectional view of a substrate being processed in accordance with a third embodiment of this invention;

Figs. 4—8A schematically represent the configuration of the device throughout the various steps of the procedure in accordance with this invention wherein Fig. 6A and Fig. 8A are sections taken along the lines 6A—6A and 8A—8A of Fig. 6 and Fig. 8, respectively;

Fig. 7 represents a cross-sectional view of a second embodiment in accordance with this invention at the point in the process after deposition of the uniform semiconductive layer in the vacuum chamber.

For a general understanding of the invention, reference is made to the drawings in which like reference characters have been used throughout to indicate like parts. Fig. 1 represents a substrate 11 such as for example, insulating materials including glass, ceramics, plastics materials such as polymethylmethacrylate, polyesters, polycarbonates, polyvinyl polymers, and the like. Further, the substrate in certain instances may be fabricated of metal materials such as aluminum, copper, tin, chromium, or other conducting metallic materials. However, when a conducting material is used as the substrate, it is necessary for the operation of the device to cover the surface thereof initially with an insulating material.

Referring specifically to Fig. 1, the substrate 11 is carefully cleaned by suitable techniques known in the art, such as degreasing, washing, rinsing, and the like, and inserted into a vacuum chamber equipped with a means for moving shadow masks in and out of position between the source of the material to be deposited and the substrate. Equipment such as this is known in the art and requires no further explanation here. Any suitable means of applying the various films throughout

this procedure in the vacuum may be employed such as, for example, evaporation, sputtering, and the like.

The vacuum is then pumped down to a pressure of less than 1.33 mNm^{-2} and preferably less than $13.3 \text{ } \mu\text{Nm}^{-2}$ and the semiconductor layer 13 is deposited onto the substrate 11.

With regard to the embodiment shown in Fig. 1, it should be noted that the semiconductor layer 13 is deposited directly onto an insulating material. Precautions may be taken to prepare the surface of the substrate 11 prior to deposition of the semiconductor layer such as, for example, plasma etching, ion milling and the like, in order to provide a new surface onto which the semiconductor layer 13 is deposited. Further, the surface of the substrate 11 may initially have deposited thereon a uniform layer 15 of an insulating material such as, for example, aluminum oxide, silicon monoxide, silicon dioxide, calcium fluoride, magnesium fluoride, and the like. In this embodiment, the substrate may be either an insulating material or a conductive material. This structure is shown in Fig. 2 wherein substrate 11 has deposited thereon a uniform insulating layer 15, and layer 15 has deposited thereon a uniform layer of any suitable semiconducting material such as, for example, cadmium selenide, tellurium, cadmium sulfide, silicon, indium arsenide, gallium arsenide, tin oxide, lead telluride, and the like. It is pointed out herein that throughout the various embodiments described herein that the semiconducting layer may be of any suitable semiconducting layers known in the thin film transistor art.

In still another embodiment shown in Fig. 3, substrate 11 has initially deposited thereon a uniform conductive layer 17 which has deposited thereon an insulating layer 15 and a semiconducting layer 13.

In the embodiment shown in Figs. 2 and 3, the semiconducting layer is always deposited upon a new surface in the vacuum. Thus, no impurities can be present because of the surface being subjected to ambient conditions. It is known that such surfaces are instrumental in the fabrication of thin film transistors having superior characteristics and, therefore, this structure is preferred herein. Additionally, this structure provides an inherent advantage in that it permits the ready adaptation of the device to also include a capacitor within each of the thin film transistor circuits fabricated.

In the remainder of the discussion herein, it should be understood that any of the structures of Figs. 1 through 3 are contemplated as representative of the appearance of the structure at this point in the process in accordance with this invention. That is, the semiconductor material 13 may be deposited directly onto the substrate 11 onto an insulating layer 15 which separates the semiconductor 13 from the substrate 11 or onto an insulating layer 15 which separates the semiconductor layer 13 from a conductive layer 17 deposited onto the substrate 11.

Referring to Fig. 4, subsequent to the deposition of the semiconductive layer 13, a shadow mask is positioned beneath the substrate 11 containing the uniform layer of semiconducting material 13 and a thin layer of an insulating material is deposited onto the surface of the semiconductive layer through the apertures of the shadow mask to form a plurality of discrete areas of insulating material 19 on the surface of the uniform layer of semiconducting material, as shown in Fig. 4. The discrete areas of insulating material are deposited generally in a thickness of from about 20 to about 200 nm and preferably from about 50 to about 100 nm thickness. The apertures in the mask and thus the discrete areas of insulating material define the conducting channels of the completed thin film transistors of the array. Any suitable insulating material may be deposited, such as any of those mentioned above.

An example of a suitable shadow mask for the deposition of four discrete rectangular-shaped areas of insulating material per square mm is a mask having 50 rows and 50 columns of rectangular openings 25 microns high and 63.5 microns wide, which rectangular areas are separated from each other by 508 microns center-to-center. Thus, such a mask will form an array of four insulating areas per square mm there being 50 insulating areas in each column and 50 insulating areas in each row.

Following the deposition of the discrete areas of insulating material 19, a uniform layer of conductive material 21, shown in Fig. 5, such as, for example, aluminum, copper, gold, silver, chromium, indium, nickel, a combination of any of these materials such as, for example, a chromium-gold-indium composition or a number of layers of the conductive material such as, for example, an initial layer of indium overcoated with a gold layer is deposited.

The structure of Fig. 5 is next removed from the vacuum. A photolithographic technique is employed in order to delineate the configuration of the source and drain and bus bar patterns to be formed from the conducting layer 21. Fig. 6 shows the metal layer 21 being removed from all areas of the array except those defined by the source bus 23 and the drain pads 25. Thus, in practice, a photoresist is applied uniformly over the surface of the structure of Fig. 5. This can be accomplished by spin coating, doctor blading, or any suitable technique known in the photoresist art. The photoresist material is then exposed photographically to render certain portions thereof soluble and others insoluble in a given solvent. The source-drain photomask is aligned with the insulating pads 19 to ensure proper position of the source and drain electrodes. In the case shown in Figs. 6 and 6A, the areas of photoresist immediately covering the source bus 23 and the drain pads 25 will remain in place and all of the rest of the photoresist material will be removed. A suitable etching solution will then be employed to remove the unprotected conductive layer 21 and also the semiconductive layer 13 immediately

beneath that portion of the conductive material that is being removed. It may be necessary to utilize a different etch for the semiconductive material from that for the conductive material, depending on the particular materials employed. In this regard, note that the areas of the conductive material 21 immediately above the insulating pads 19 are etched away, but the insulating pads 19 protect the semiconductive material 13 immediately therebeneath thus forming the conductive channel between the source buses 23 and their corresponding drain pads 25. A suitable photoresist material for this process is Shipley AZ 1350 J sold by Shipley Co., Inc., Newton, Mass. Finally, the remainder of the photoresist protecting the metal forming the source buses 23 and drain pads 25 is removed. The structure now has the configuration shown in Figs. 6 and 6A.

The next step in the procedure towards the completion of the thin film transistor array and shown in Fig. 7 is the deposition of a uniform insulating layer 27 over the structure of Figs. 6 and 6A which forms the gate insulator of the thin film transistors. This can be accomplished by any suitable technique known in this art for the deposition of an insulating layer including once again placing the substrate containing the layers previously formed, as described above, into a suitable vacuum device and applying a uniform layer of a suitable insulator such as those mentioned above, for example, by evaporation or sputtering. During this pump-down, a uniform layer of a suitable conducting material is deposited over the insulating layer 27. The assembly may then be removed from the vacuum and the gates 29 and gate buses 31, see Figs. 8 and 8A, fabricated by a photolithographic technique such as that described above with regard to the fabrication of the source buses 23 and drain pads 25.

Thus, the process described for the preparation of a thin film transistor array is advantageous for the reason that all of the interfaces between the semiconductor and the next adjacent layers and between the source and drain contacts are deposited in a single vacuum pump-down and, therefore, the characteristics of thin film transistors prepared by this one-pump-down technique are preserved. Secondly, as there is only one layer of material deposited through one patterned aperture mask, there is no requirement for mask registration inside the vacuum system. This enables the use of a simple vacuum system to accomplish the preparation.

Finally, it may be desirable to anneal the completed TFT structure, such as by heating in a non-oxidizing atmosphere such as nitrogen for about 10 hours at about 350°C.

In a prepared process in accordance with this invention, a glass substrate is positioned in a vacuum device and a conductive layer 17, such as that shown in Fig. 3, the conductive material being a 100 nm thick aluminum layer, is deposited thereon. Following the deposition of the aluminum layer, a 400 nm thick aluminum oxide (Al_2O_3) layer is uniformly deposited over the

aluminum layer. This layer is shown as layer 15 in Fig. 3: Once again, in accordance with that depicted in Fig. 3, a uniform layer of about 10 nm thick of cadmium selenide is uniformly deposited over the aluminum oxide layer. A mask having two apertures per linear mm is moved into position beneath the surface of the cadmium selenide semiconductive layer 13 and a layer of from about 50 to 100 nm thick of aluminum oxide is evaporated through the apertures in the mask to form the discrete areas shown as 19 in Figs. 4 through 8A. The shadow mask is removed from its position beneath the semiconductive layer 13 and a uniform layer of 10 nm thick of indium followed by a 100 nm thick gold layer is deposited over the entire surface of the assembly. This assembly is then removed from the vacuum system and a layer of Shipley AZ 1350 J photoresist is spin coated over the surface thereof. This photoresist is then exposed through a mask which delineates the areas to be removed from the conductive layer 21. The particular resist utilized herein is chemically altered in order that it is readily removed in exposed regions by treatment with aqueous solutions. The unwanted areas of the photoresist are then washed away leaving the areas, which are designated 23 and 25 in Fig. 6, covered with a resist material. A suitable etch for the conductive layer, that is, the indium and gold layers is then applied. A particularly suitable solution is about 3 parts HCl and about 1 part HNO₃. Further, the exposed regions of the semiconductive layer 13 are also etched away at the same time. The resist material immediately above the source and drain pads is now removed by application of acetone. The assembly thus produced is once again inserted into a vacuum and a 300 nm thick aluminum oxide layer 27 is uniformly coated thereon. Following the application of the aluminum oxide layer, the gate electrodes 29 and the gate buses 31 are applied by evaporation of a 100 nm thick uniform aluminum layer over the surface of the insulating layer 27. The assembly is then removed from the vacuum and utilizing a similar photolithographic technique, the gates 29 and the gate buses 31 are delineated. Finally, windows through the Al₂O₃ layer 27 to expose the drain pads are etched.

It is, of course, to be understood that the particular steps with respect to the preparation of the final layers, as set forth in the specific example immediately above, are for exemplary purposes and that these layers may be formed by other suitable techniques, for example, the gates and gate bus bars 31 may be formed by evaporation through a shadow mask directly onto the surface of the insulating layer 27 while within the same vacuum pump-down. Also, the insulating layer 27 may be fabricated of a suitable resinous material.

The structure of a portion of a thin film transistor array in accordance with this invention is shown in Figs. 8 and 8A. As indicated above, the structure of the array may be modified by disposing the semiconductive layer 13 on top of insulat-

ing layer 15 which itself may lie either adjacent either a conductive layer 17 or the substrate 11. In any event, the semiconductor material 13 in the completed array is coterminous with the source electrodes, source bus conductors and the drain electrodes. That is, the semiconductive material 13 is in physical and electrical contact with the conductive material forming the source electrodes and source bus conductors 23 and the drain electrodes 25 in all areas except in the areas which form the conductive channel of each transistor, this area being that portion of the semiconductor material 13 lying immediately beneath the insulating pads 19. Thus, all of the source electrodes 23 in any column are electrically connected together since each source electrode forms a portion of the source bus conductor. By electrically addressing any given column source bus conductor 23 and any given row gate bus conductor, a single transistor of the array can be turned on, thereby permitting current flow from its source through the conductive channel of the semiconductive material to the corresponding drain. This then can be utilized to alter the field across an electro-optical device, such as a liquid crystal layer, thus providing an optical read-out of a bit of information.

Claims

1. A method of making an array of thin film transistors which comprises depositing *in vacuo* on an insulative substrate (11) a uniform layer (13) of a semiconductive material, depositing on the semiconductive layer, through a shadow mask, a plurality of discrete areas (19) of an insulation material defining the conductive channels of the completed thin film transistors; depositing a uniform layer (21) of a conductive material over the areas of insulation material and exposed portions of the semiconductive layer; removing the vacuum; photolithographically forming a masking layer on the uniform layer of conductive material having a predetermined pattern of openings therein aligned with the insulating pads (19) in order to delineate the configuration of the source, drain and busbar patterns to be formed from the layer of conductive material (21); removing the portions of the conductive material unprotected by the masking layer thereby to form the source, drain and source bus conductors of the array; removing the semiconductive material exposed by removal of the conductive material and not protected by the discrete areas of insulation material (19); removing the masking layer; depositing a uniform layer (27) of insulation material over the thus-formed structure to form, in combination with the insulating pads the gate insulator of the thin film transistors, and depositing in discrete areas a layer of conductive material which is selectively delineated photolithographically to form the gate (29) and gate bus conductors (31) of the array.

2. The method of claim 1 wherein, prior to the deposition of the uniform layer semiconductive

material onto the substrate, the substrate is subjected to a treatment step to provide a new surface.

3. The method of claim 2, wherein the surface of the substrate is subjected to ion milling.

4. The method of claim 2, wherein the surface of the substrate is plasma etched.

5. The method of any preceding claim, wherein prior to the deposition of the uniform layer of semiconductive material on the substrate, a uniform layer (15) of an insulation material is deposited on the substrate.

6. The method of any of claims 1—4 wherein, prior to the deposition of the uniform layer of semiconductive material on the substrate, a uniform layer (17) of a conductive material is deposited on the substrate, and a uniform layer (15) of an insulation material is deposited on the conductive material.

Patentansprüche

1. Verfahren zum Herstellen einer Anordnung von Dünnschicht-Transistoren, bei dem im Vakuum auf ein isolierendes Substrat (11) eine gleichförmige Schicht (13) aus einem Halbleitermaterial aufgebracht wird, auf der Halbleiterschicht durch eine Schattenmaske hindurch eine Veilzahl von diskreten Bereichen (19) aus einem isolierenden Material aufgebracht wird, die die leitenden Kanäle des fertigen Dünnschicht-Transistors festlegen, eine gleichförmige Schicht (21) aus einem leitenden Material über den Bereichen aus isolierendem Material und den freien Bereichen der Halbleiterschicht aufgebracht wird, das Vakuum entfernt wird, fotolithographisch eine Maskierungsschicht auf der gleichförmigen Schicht aus leitendem Material gebildet wird, die ein vorbestimmtes Öffnungsmuster aufweist, das mit den isolierenden Bereichen (19) ausgerichtet wird, um die Ausgestaltung der Source-, Drain- und Sammelschienenmuster zu begrenzen, die aus der Schicht aus leitendem Material (21) zu bilden sind, die von der Maskierungsschicht ungeschützten Bereiche des leitenden Materials entfernt werden, um dadurch die Leiter für die Source-, Drain- und Source-Sammelschienen der Anordnung zu bilden, das Halbleitermaterial entfernt wird, welches durch Entfernen des leitenden Materials freigesetzt wird und durch die diskreten Bereiche aus isolierenden Material (19) nicht geschützt ist, die Maskierungsschicht entfernt wird, eine gleichförmige Schicht (27) aus isolierendem Material auf der derart gebildeten Struktur aufgebracht wird, um in Kombination mit den isolierenden Bereichen den Gate-Isolator des Dünnschicht-Transistors zu bilden, und in diskreten Bereichen eine Schicht aus leitendem Material aufgebracht wird, die wahlweise fotolithographisch aufgezeichnet wird, um das Gate (29) und die Gate-Sammelleitung (31) der Anordnung zu bilden.

2. Verfahren nach Anspruch 1, bei dem vor dem Aufbringen der gleichförmigen Halbleiter-

materialschicht auf dem Substrat das Substrat einem Behandlungsschritt ausgesetzt wird, eine neue Oberfläche zu schaffen.

3. Verfahren nach Anspruch 2, bei dem die Oberfläche des Substrats einem Ionenfräsen ausgesetzt wird.

4. Verfahren nach Anspruch 2, bei dem die Oberfläche des Substrats plasmageätzt wird.

5. Verfahren nach einem der vorhergehenden Ansprüche, bei dem vor dem Aufbringen der gleichförmigen Halbleitermaterialschicht auf dem Substrat eine gleichförmige Schicht (15) aus einem Isoliermaterial auf das Substrat aufgebracht wird.

6. Verfahren nach einem der Ansprüche 1 bis 4, bei dem vor dem Aufbringen der gleichförmigen Halbleitermaterialschicht auf das Substrat eine gleichförmige Schicht (17) aus einem leitenden Material auf das Substrat aufgebracht wird und eine gleichförmige Schicht (15) aus einem isolierenden Material auf das leitende Material aufgebracht wird.

Revendications

1. Procédé de fabrication d'un réseau de transistors à couche mince, qui comprend le dépôt *sous vide* sur un substrat isolant (11) d'une couche uniforme (13) d'un matériau semi-conducteur, le dépôt sur la couche en semi-conducteur, par l'intermédiaire d'un masque, d'une multitude de zones discrètes (19) d'un matériau isolant définissant les canaux conducteurs des transistors à couche mince complétés; le dépôt d'une couche uniforme (21) d'un matériau conducteur sur les zones en matériau isolant et des parties exposées de la couche en semi-conducteur; l'élimination du vide; la formation photolithographique d'une couche de masquage sur la couche uniforme de matériau conducteur ayant un profil prédéterminé d'ouvertures qui sont alignées avec les pastilles isolantes (19) dans le but de tracer la configuration de la source, du drain et des motifs des bus devant être formés à partir de la couche en matériau conducteur (21); l'enlèvement des parties du matériau conducteur non protégé par la couche de masquage de manière à former la source, le drain et les conducteurs de bus de la source du réseau; l'enlèvement du matériau semi-conducteur exposé par l'enlèvement du matériau conducteur et non protégé par les zones discrètes du matériau isolant (19); l'enlèvement de la couche de masquage; le dépôt d'une couche uniforme (27) de matériau isolant sur la structure ainsi formée de manière à obtenir en combinaison avec les pastilles isolantes, l'isolant de grille des transistors à couche mince, et le dépôt dans des zones discrètes d'une couche de matériau conducteur qui est sélectivement tracée photolithographiquement de manière à former la grille (29) et les conducteurs (31) de bus de grille de réseau.

2. Procédé selon la revendication 1, dans lequel avant le dépôt du matériau semi-conduc-

teur en couche uniforme sur le substrat, le substrat est soumis à une étape de traitement de manière à obtenir une nouvelle surface.

3. Procédé selon la revendication 2, dans lequel la surface du substrat est soumise à un fraisage ionique.

4. Procédé selon la revendication 2, dans lequel la surface du substrat est attaquée par plasma.

5. Procédé selon l'une quelconque des revendications précédentes, dans lequel, avant le dépôt

de la couche uniforme en matériau semi-conducteur sur le substrat, une couche uniforme (15) d'un matériau isolant est déposée sur le substrat.

6. Procédé selon l'une quelconque des revendications 1 à 4, dans lequel avant le dépôt de la couche uniforme en matériau semi-conducteur sur le substrat, une couche uniforme (17) d'un matériau conducteur est déposée sur le substrat, et une couche uniforme (15) d'un matériau isolant est déposée sur le matériau conducteur.

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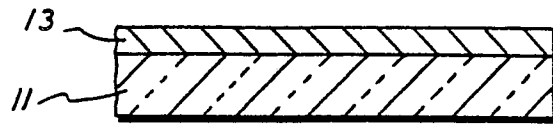


FIG. 1

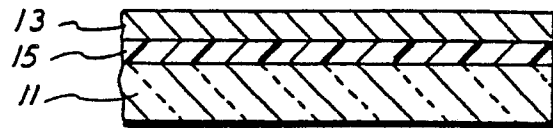


FIG. 2

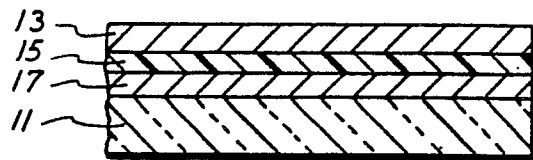


FIG. 3

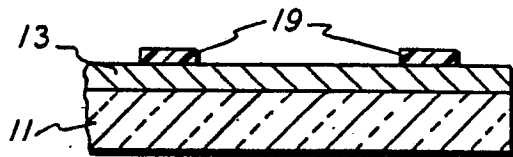


FIG. 4

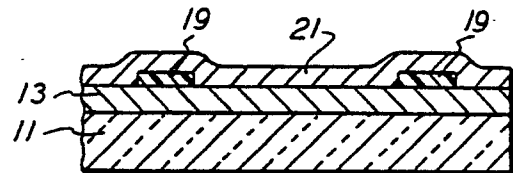


FIG. 5

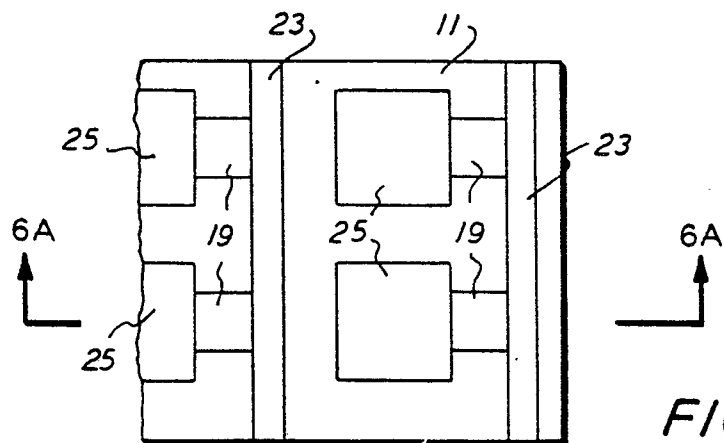


FIG. 6

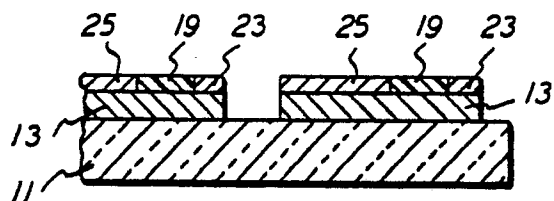


FIG. 6A

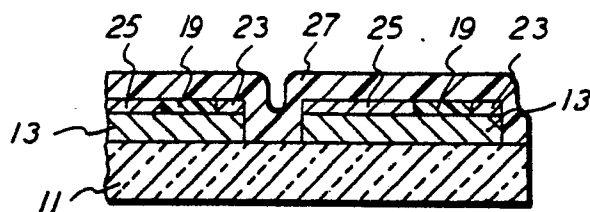


FIG. 7

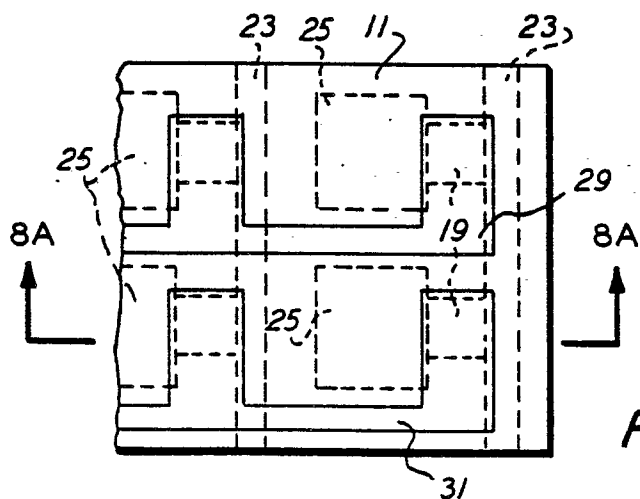


FIG. 8

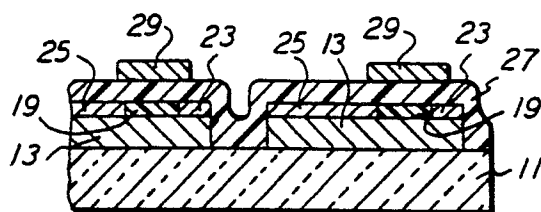


FIG. 8A